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NXP Semiconductors
Data Sheet: Advance Information

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S32K1XX

S32K1xx Data Sheet

Notes

- Technical information for S32K118 device is preliminary, until this device achieves qualification.
- Following two are the available attachments with Datasheet:
  - S32K1xx_Orderable_Part_Number_ List.xlsx
  - S32K1xx_Power_Modes_Configuration.xlsx

Key Features

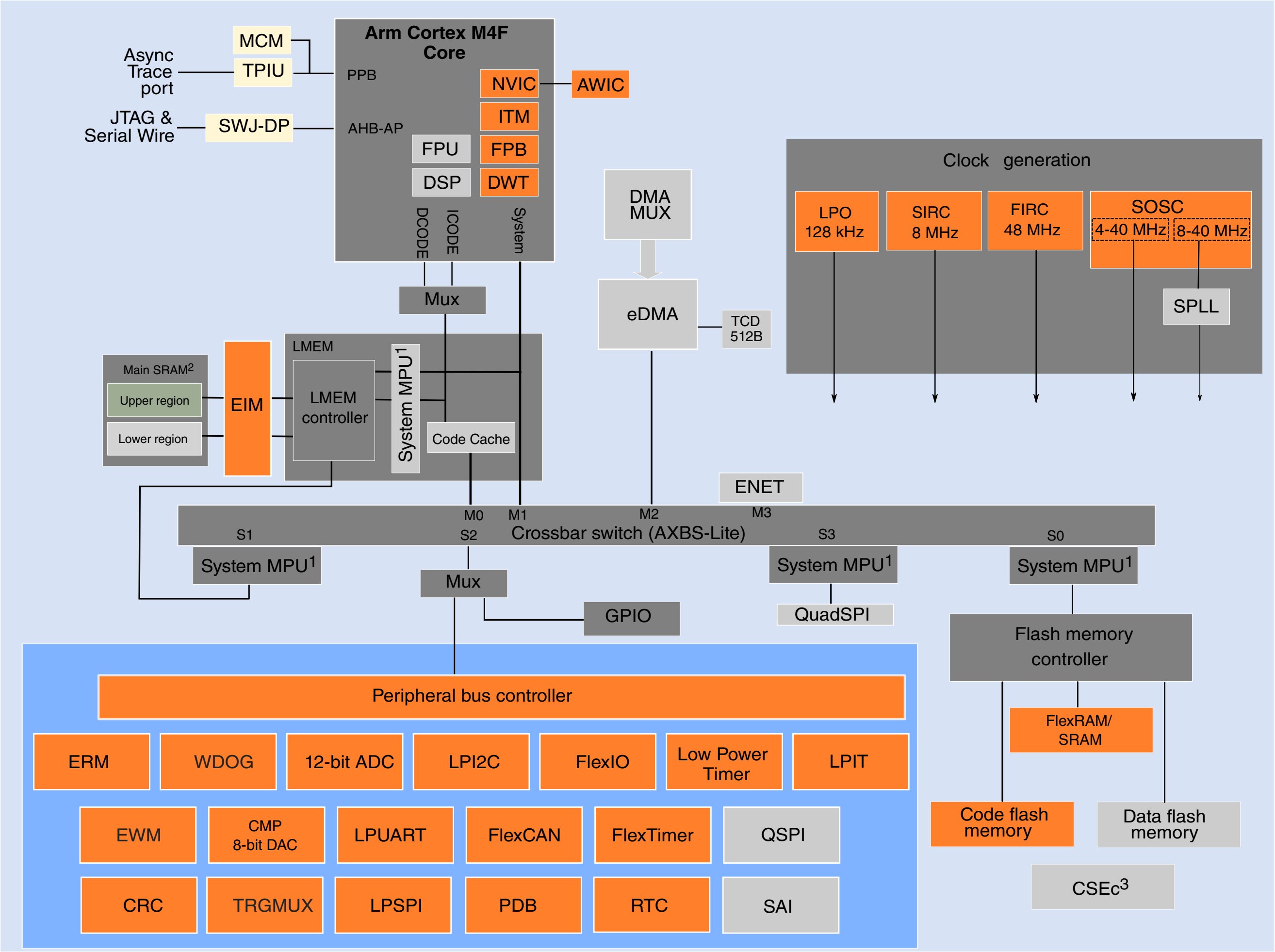
- Operating characteristics
  - Voltage range: 2.7 V to 5.5 V
  - Ambient temperature range: -40 °C to 105 °C for HSRUN mode, -40 °C to 125 °C for RUN mode
- Arm™ Cortex-M4F/M0+ core, 32-bit CPU
  - Supports up to 112 MHz frequency (HSRUN mode) with 1.25 Dhrystone MIPS per MHz
  - Arm Core based on the Armv7 Architecture and Thumb®-2 ISA
  - Integrated Digital Signal Processor (DSP)
  - Configurable Nested Vectored Interrupt Controller (NVIC)
  - Single Precision Floating Point Unit (FPU)
- Clock interfaces
  - 4 - 40 MHz fast external oscillator (SOSC)
  - 48 MHz Fast Internal RC oscillator (FIRC)
  - 8 MHz Slow Internal RC oscillator (SIRC)
  - 128 kHz Low Power Oscillator (LPO)
  - Up to 112 MHz (HSRUN) System Phased Lock Loop (SPLL)
  - Up to 50 MHz DC external square wave input clock
  - Real Time Counter (RTC)
- Power management
  - Low-power Arm Cortex-M4F/M0+ core with excellent energy efficiency
  - Power Management Controller (PMC) with multiple power modes: HSRUN, RUN, STOP, VLPR, and VLPS. Note: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 Mhz) to execute CSEc (Security) or EEPROM writes/erase.
  - Clock gating and low power operation supported on specific peripherals.
- Memory and memory interfaces
  - Up to 2 MB program flash memory with ECC
  - 64 KB FlexNVM for data flash memory with ECC and EEPROM emulation. Note: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.
  - Up to 256 KB SRAM with ECC
  - Up to 4 KB of FlexRAM for use as SRAM or EEPROM emulation
  - Up to 4 KB Code cache to minimize performance impact of memory access latencies
  - QuadSPI with HyperBus™ support
- Mixed-signal analog
  - Up to two 12-bit Analog-to-Digital Converter (ADC) with up to 32 channel analog inputs per module
  - One Analog Comparator (CMP) with internal 8-bit Digital to Analog Converter (DAC)
- Debug functionality
  - Serial Wire JTAG Debug Port (SWJ-DP) combines
  - Debug Watchpoint and Trace (DWT)
  - Instrumentation Trace Macrocell (ITM)
  - Test Port Interface Unit (TPIU)
  - Flash Patch and Breakpoint (FPB) Unit
- Human-machine interface (HMI)
  - Up to 156 GPIO pins with interrupt functionality
  - Non-Maskable Interrupt (NMI)

- Communications interfaces
  - Up to three Low Power Universal Asynchronous Receiver/Transmitter (LPUART/LIN) modules with DMA support and low power availability
  - Up to three Low Power Serial Peripheral Interface (LPSPI) modules with DMA support and low power availability
  - Up to two Low Power Inter-Integrated Circuit (LPI2C) modules with DMA support and low power availability
  - Up to three FlexCAN modules (with optional CAN-FD support)
  - FlexIO module for emulation of communication protocols and peripherals (UART, I2C, SPI, I2S, LIN, PWM, etc).
  - Up to one 10/100Mbps Ethernet with IEEE1588 support and two Synchronous Audio Interface (SAI) modules.
- Safety and Security
  - Cryptographic Services Engine (CSEc) implements a comprehensive set of cryptographic functions as described in the SHE (Secure Hardware Extension) Functional Specification. Note: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.
  - 128-bit Unique Identification (ID) number
  - Error-Correcting Code (ECC) on flash and SRAM memories
  - System Memory Protection Unit (System MPU)
  - Cyclic Redundancy Check (CRC) module
  - Internal watchdog (WDOG)
  - External Watchdog monitor (EWM) module
- Timing and control
  - Up to eight independent 16-bit FlexTimers (FTM) modules, offering up to 64 standard channels (IC/OC/PWM)
  - One 16-bit Low Power Timer (LPTMR) with flexible wake up control
  - Two Programmable Delay Blocks (PDB) with flexible trigger system
  - One 32-bit Low Power Interrupt Timer (LPIT) with 4 channels
  - 32-bit Real Time Counter (RTC)
- Package
  - 32-pin QFN, 48-pin LQFP, 64-pin LQFP, 100-pin LQFP, 100-pin MAPBGA, 144-pin LQFP, 176-pin LQFP package options
- 16 channel DMA with up to 63 request sources using DMAMUX

Table of Contents

1 Block diagram

Following figures show superset high level architecture block diagrams of S32K14x series and S32K11x series respectively. Other devices within the family have a subset of the features. See Feature comparison for chip specific values.



1: On this device, NXP's system MPU implements the safety mechanisms to prevent masters from accessing restricted memory regions. This system MPU provides memory protection at the level of the Crossbar Switch. Each Crossbar master (Core, DMA, Ethernet) can be assigned different access rights to each protected memory region. The Arm M4 core version in this family does not integrate the Arm Core MPU, which would concurrently monitor only core-initiated memory accesses. In this document, the term MPU refers to NXP's system MPU.

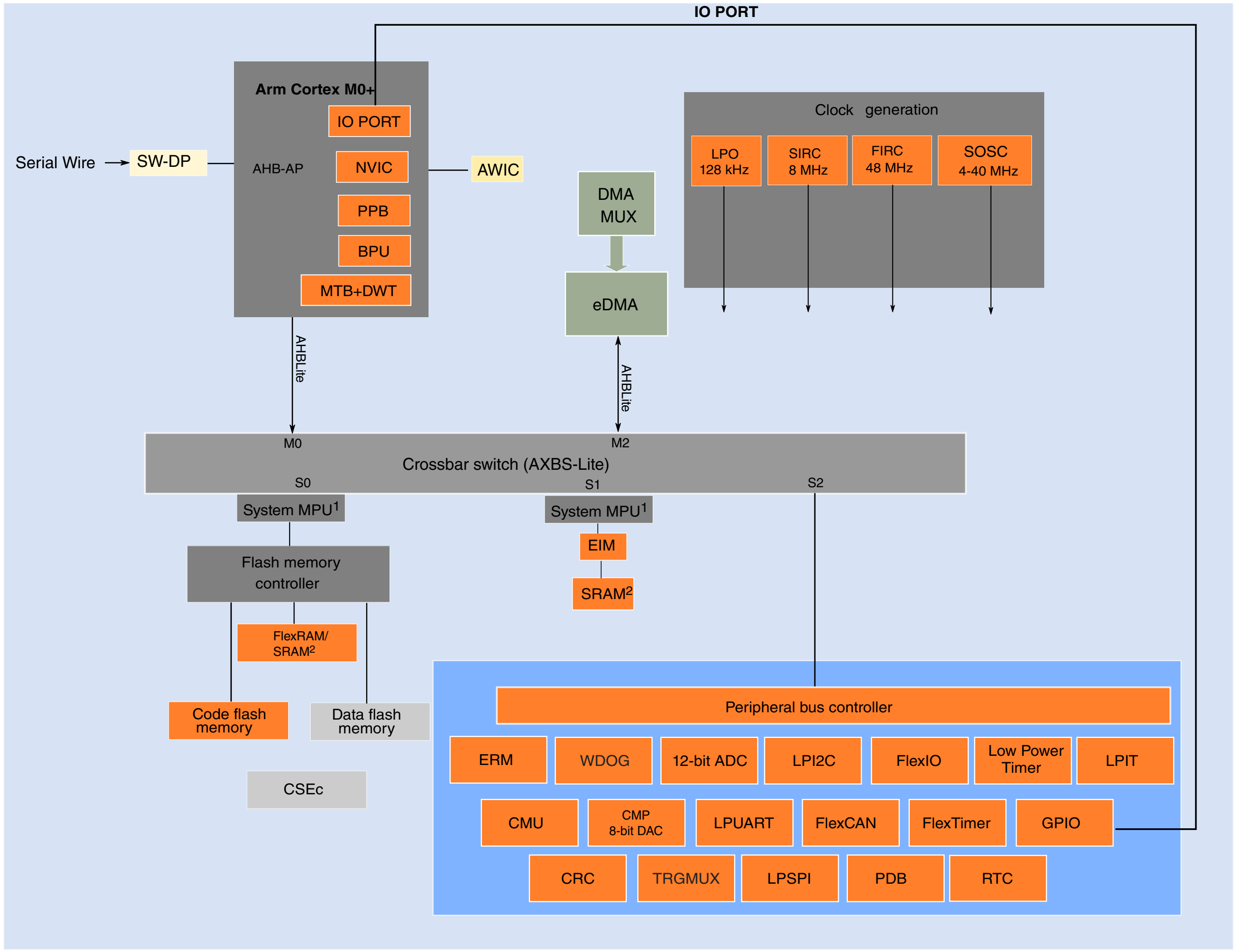
2: For the device-specific sizes, see the "On-chip SRAM sizes" table in the "Memories and Memory Interfaces" chapter of the S32K1xx Series Reference Manual.

3: CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.

Key:

- Device architectural IP on all S32K devices
- Peripherals present on all S32K devices
- Peripherals present on selected S32K devices (see the "Feature Comparison" section)

Figure 1. High-level architecture diagram for the S32K14x family



1: On this device, NXP's system MPU implements the safety mechanisms to prevent masters from accessing restricted memory regions. This system MPU provides memory protection at the level of the Crossbar Switch. Crossbar master (Core, DMA) can be assigned different access rights to each protected memory region. The Arm M0+ core version in this family does not integrate the Arm Core MPU, which would concurrently monitor only core-initiated memory accesses. In this document, the term MPU refers to NXP's system MPU.

2: For the device-specific sizes, see the "On-chip SRAM sizes" table in the "Memories and Memory Interfaces" chapter of the S32K1xx Series Reference Manual.

Key:
- Device architectural IP on all S32K devices
- Peripherals present on all S32K devices
- Peripherals present on selected S32K devices (see the "Feature Comparison" section)

Figure 2. High-level architecture diagram for the S32K11x family

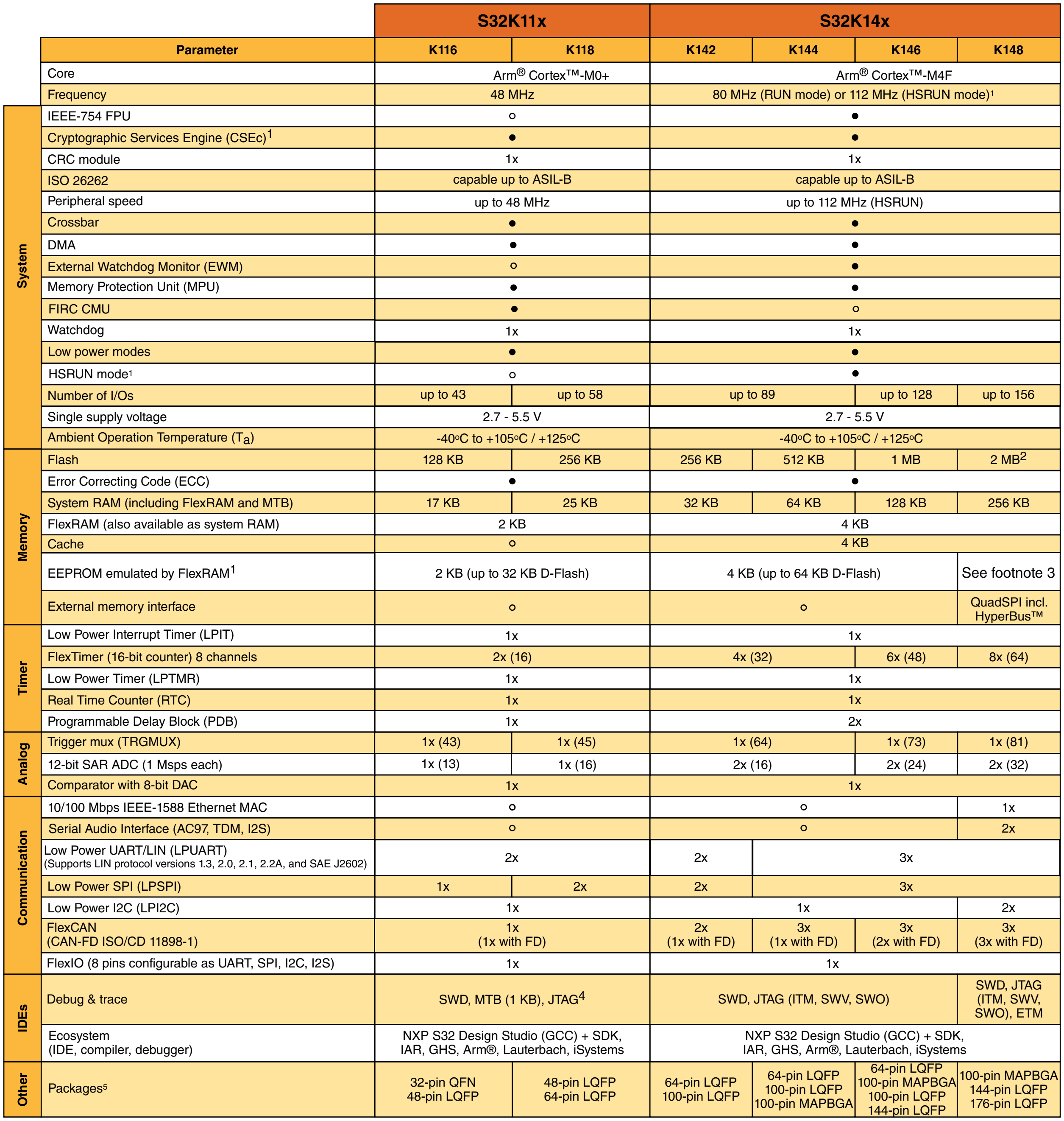
2 Feature comparison

The following figure summarizes the memory, peripherals and packaging options for the S32K1xx devices. All devices which share a common package are pin-to-pin compatible.

NOTE

Availability of peripherals depends on the pin availability in a particular package. For more information see *IO Signal*

Description Input Multiplexing sheet(s) attached with Reference Manual.



		S32K11x		S32K14x			
	Parameter	**K116**	**K118**	**K142**	**K144**	**K146**	**K148**
	Core	Arm® Cortex™-M0+		Arm® Cortex™-M4F			
	Frequency	48 MHz		80 MHz (RUN mode) or 112 MHz (HSRUN mode)[1]			
System	IEEE-754 FPU	○		●			
	Cryptographic Services Engine (CSEc)[1]	●		●			
	CRC module	1x		1x			
	ISO 26262	capable up to ASIL-B		capable up to ASIL-B			
	Peripheral speed	up to 48 MHz		up to 112 MHz (HSRUN)			
	Crossbar	●		●			
	DMA	●		●			
	External Watchdog Monitor (EWM)	○		●			
	Memory Protection Unit (MPU)	●		●			
	FIRC CMU	●		○			
	Watchdog	1x		1x			
	Low power modes	●		●			
	HSRUN mode[1]	○		●			
	Number of I/Os	up to 43	up to 58	up to 89		up to 128	up to 156
	Single supply voltage	2.7 - 5.5 V		2.7 - 5.5 V			
	Ambient Operation Temperature (T_a)	-40°C to +105°C / +125°C		-40°C to +105°C / +125°C			
Memory	Flash	128 KB	256 KB	256 KB	512 KB	1 MB	2 MB[2]
	Error Correcting Code (ECC)	●		●			
	System RAM (including FlexRAM and MTB)	17 KB	25 KB	32 KB	64 KB	128 KB	256 KB
	FlexRAM (also available as system RAM)	2 KB		4 KB			
	Cache	○		4 KB			
	EEPROM emulated by FlexRAM[1]	2 KB (up to 32 KB D-Flash)		4 KB (up to 64 KB D-Flash)			See footnote 3
	External memory interface	○		○			QuadSPI incl. HyperBus™
Timer	Low Power Interrupt Timer (LPIT)	1x		1x			
	FlexTimer (16-bit counter) 8 channels	2x (16)		4x (32)		6x (48)	8x (64)
	Low Power Timer (LPTMR)	1x		1x			
	Real Time Counter (RTC)	1x		1x			
	Programmable Delay Block (PDB)	1x		2x			
Analog	Trigger mux (TRGMUX)	1x (43)	1x (45)	1x (64)		1x (73)	1x (81)
	12-bit SAR ADC (1 Msps each)	1x (13)	1x (16)	2x (16)		2x (24)	2x (32)
	Comparator with 8-bit DAC	1x		1x			
Communication	10/100 Mbps IEEE-1588 Ethernet MAC	○		○			1x
	Serial Audio Interface (AC97, TDM, I2S)	○		○			2x
	Low Power UART/LIN (LPUART) (Supports LIN protocol versions 1.3, 2.0, 2.1, 2.2A, and SAE J2602)	2x		2x	3x		
	Low Power SPI (LPSPI)	1x	2x	2x	3x		
	Low Power I2C (LPI2C)	1x		1x			2x
	FlexCAN (CAN-FD ISO/CD 11898-1)	1x (1x with FD)		2x (1x with FD)	3x (1x with FD)	3x (2x with FD)	3x (3x with FD)
	FlexIO (8 pins configurable as UART, SPI, I2C, I2S)	1x		1x			
IDEs	Debug & trace	SWD, MTB (1 KB), JTAG[4]		SWD, JTAG (ITM, SWV, SWO)			SWD, JTAG (ITM, SWV, SWO), ETM
	Ecosystem (IDE, compiler, debugger)	NXP S32 Design Studio (GCC) + SDK, IAR, GHS, Arm®, Lauterbach, iSystems		NXP S32 Design Studio (GCC) + SDK, IAR, GHS, Arm®, Lauterbach, iSystems			
Other	Packages[5]	32-pin QFN 48-pin LQFP	48-pin LQFP 64-pin LQFP	64-pin LQFP 100-pin LQFP	64-pin LQFP 100-pin LQFP 100-pin MAPBGA	64-pin LQFP 100-pin MAPBGA 100-pin LQFP 144-pin LQFP	100-pin MAPBGA 144-pin LQFP 176-pin LQFP

LEGEND:

- ○ Not implemented
- ● Available on the device

1 No write or erase access to Flash module, including Security (CSEc) and EEPROM commands, are allowed when device is running at HSRUN mode (112MHz) or VLPR mode.
2 Available when EEEPROM, CSEc and Data Flash are not used. Else only up to 1,984 KB is available for Program Flash.
3 4 KB (up to 512 KB D-Flash as a part of 2 MB Flash). Up to 64 KB of flash is used as EEPROM backup and the remaining 448 KB of the last 512 KB block can be used as Data flash or Program flash. See chapter FTFC for details.
4 Only for Boundary Scan Register
5 See Dimensions section for package drawings

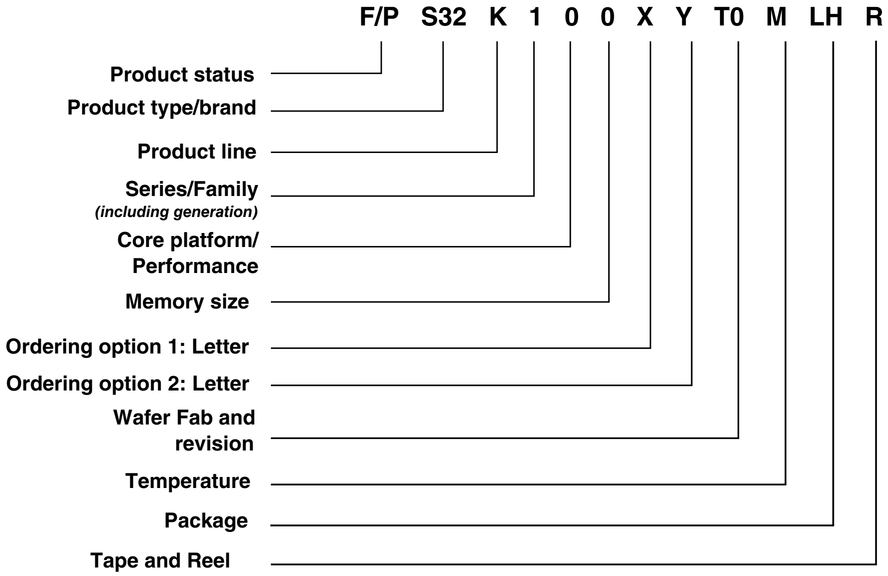
Figure 3. S32K1xx product series comparison

3 Ordering information

3.1 Selecting orderable part number

Not all part number combinations are available. See the attachment *S32K1xx_Orderable_Part_Number_ List.xlsx* attached with the Datasheet for a list of standard orderable part numbers.

3.2 Ordering information



Product status
P: Prototype
F: Qualified

Product type/brand
S32: Automotive 32-bit MCU

Product line
K: Arm Cortex MCUs

Series/Family
1: 1st product series
2: 2nd product series

Core platform/Performance
1: Arm Cortex M0+
4: Arm Cortex M4F

Memory size

	2	4	6	8
S32K11x			128K	256K
S32K14x	256K	512K	1M	2M

Ordering option
X: Speed
  B: 48 MHz without DMA (S32K11x only)
  L: 48 MHz with DMA (S32K11x only)
  H: 80 MHz
  U[1]: 112 MHz (Not valid with M temperature/125C)

Y: Optional feature
  R: Base feature set
  F: CAN FD, FlexIO
  A[1]: CAN FD, FlexIO, Security
  E: Ethernet, Serial Audio Interface (S32K148 only)
  J[1]: Ethernet, Serial Audio Interface, CAN FD, FlexIO, Security (S32K148 only)

Wafer, Fab and revision
Fx: ATMC[2]
Tx: GF
XX: Flex #[2]

x0: 1st revision

Temperature
V: -40C to 105C
M: -40C to 125C
W: -40C to 150C[2]

Package

Pins	LQFP	QFN	BGA
32	-	FM	-
48	LF	-	-
64	LH	-	-
100	LL	-	MH
144	LQ	-	-
176	LU	-	-

Tape and Reel
T: Trays/Tubes
R: Tape and Reel

1. CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.
2. Not supported yet
3. Part numbers no longer offered as standard include:
   Ordering Option X (M:64MHz); Ordering Option Y (N: limited RAM. 16KB for K142, 48KB for K144, 96KB for K146, 192KB for K148
   S: Security); Temperature (C: -40C to 85C)

NOTE

Not all part number combinations are available. See S32K1xx_Orderable_Part_Number_List.xlsx attached with the Datasheet for list of standard orderable parts.

Figure 4. Ordering information

4 General

4.1 Absolute maximum ratings

NOTE

- Functional operating conditions appear in the DC electrical characteristics. Absolute maximum ratings are stress ratings only, and functional operation at the maximum values is not guaranteed. See footnotes in the following table for specific conditions.
- Stress beyond the listed maximum values may affect device reliability or cause permanent damage to the device.
- All the limits defined in the datasheet specification must be honored together and any violation to any one or more will not guarantee desired operation.
- Unless otherwise specified, all maximum and minimum values in the datasheet are across process, voltage, and temperature.

Table 1. Absolute maximum ratings

Symbol	Parameter	Conditions[1]	Min	Max	Unit
V_{DD}[2]	2.7 V - 5. 5V input supply voltage	—	-0.3	5.8 [3]	V
V_{REFH}	3.3 V / 5.0 V ADC high reference voltage	—	-0.3	5.8 [3]	V
$I_{INJPAD\_DC\_ABS}$[4]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	—	-3	+3	mA
V_{IN_DC}	Continuous DC Voltage on any I/O pin with respect to V_{SS}	—	-0.8	5.8[5]	V
$I_{INJSUM\_DC\_ABS}$	Sum of absolute value of injected currents on all the pins (Continuous DC limit)	—	—	30	mA
T_{ramp}[6]	ECU supply ramp rate	—	0.5 V/min	500 V/ms	—
T_{ramp_MCU}[7]	MCU supply ramp rate	—	0.5 V/min	100 V/ms	—
T_A[8]	Ambient temperature	—	-40	125	°C
T_{STG}	Storage temperature	—	-55	165	°C
$V_{IN\_TRANSIENT}$	Transient overshoot voltage allowed on I/O pin beyond $V_{IN\_DC\ limit}$	—	—	6.8 [9]	V

1. All voltages are referred to V_{SS} unless otherwise specified.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. 60 s lifetime – No restrictions i.e. The part can switch.

   10 hours lifetime – Device in reset i.e. The part cannot switch.

4. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.
5. While respecting the maximum current injection limit
6. This is the Electronic Control Unit (ECU) supply ramp rate and not directly the MCU ramp rate. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
7. This is the MCU supply ramp rate and the ramp rate assumes that the S32K1xx HW design guidelines in AN5426 are followed. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
8. T_J (Junction temperature)=135 °C. Assumes T_A=125 °C for RUN mode

   T_J (Junction temperature)=125 °C. Assumes TA=105 °C for HSRUN mode

   - Assumes maximum θJA for 2s2p board. See Thermal characteristics
9. 60 seconds lifetime; device in reset (no outputs enabled/toggling)

4.2 Voltage and current operating requirements

NOTE

Device functionality is guaranteed up to the LVR assert level, however electrical performance of 12-bit ADC, CMP with 8-bit DAC, IO electrical characteristics, and communication modules electrical characteristics would be degraded when voltage drops below 2.7 V

Table 2. Voltage and current operating requirements [1]

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}[2]	Supply voltage	2.7[3]	5.5	V	4
V_{DD_OFF}	Voltage allowed to be developed on V_{DD} pin when it is not powered from any external power supply source.	0	0.1	V	
V_{DDA}	Analog supply voltage	2.7	5.5	V	4
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	– 0.1	0.1	V	4
V_{REFH}	ADC reference voltage high	2.7	V_{DDA} + 0.1	V	5
V_{REFL}	ADC reference voltage low	-0.1	0.1	V	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	6
$I_{INJPAD\_DC\_OP}$[7]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	-3	+3	mA	
$I_{INJSUM\_DC\_OP}$	Continuous total DC input current that can be injected across all I/O pins such that there's no degradation in accuracy of analog modules: ADC and ACMP (See section Analog Modules)	—	30	mA	

1. Typical conditions assumes V_{DD} = V_{DDA} = V_{REFH} = 5 V, temperature = 25 °C and typical silicon process unless otherwise stated.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
4. V_{DD} and V_{DDA} must be shorted to a common source on PCB. The differential voltage between V_{DD} and V_{DDA} is for RF-AC only. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC.

5. V_{REFH} should always be equal to or less than V_{DDA} + 0.1 V and V_{DD} + 0.1 V
6. Open drain outputs must be pulled to V_{DD}.
7. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.

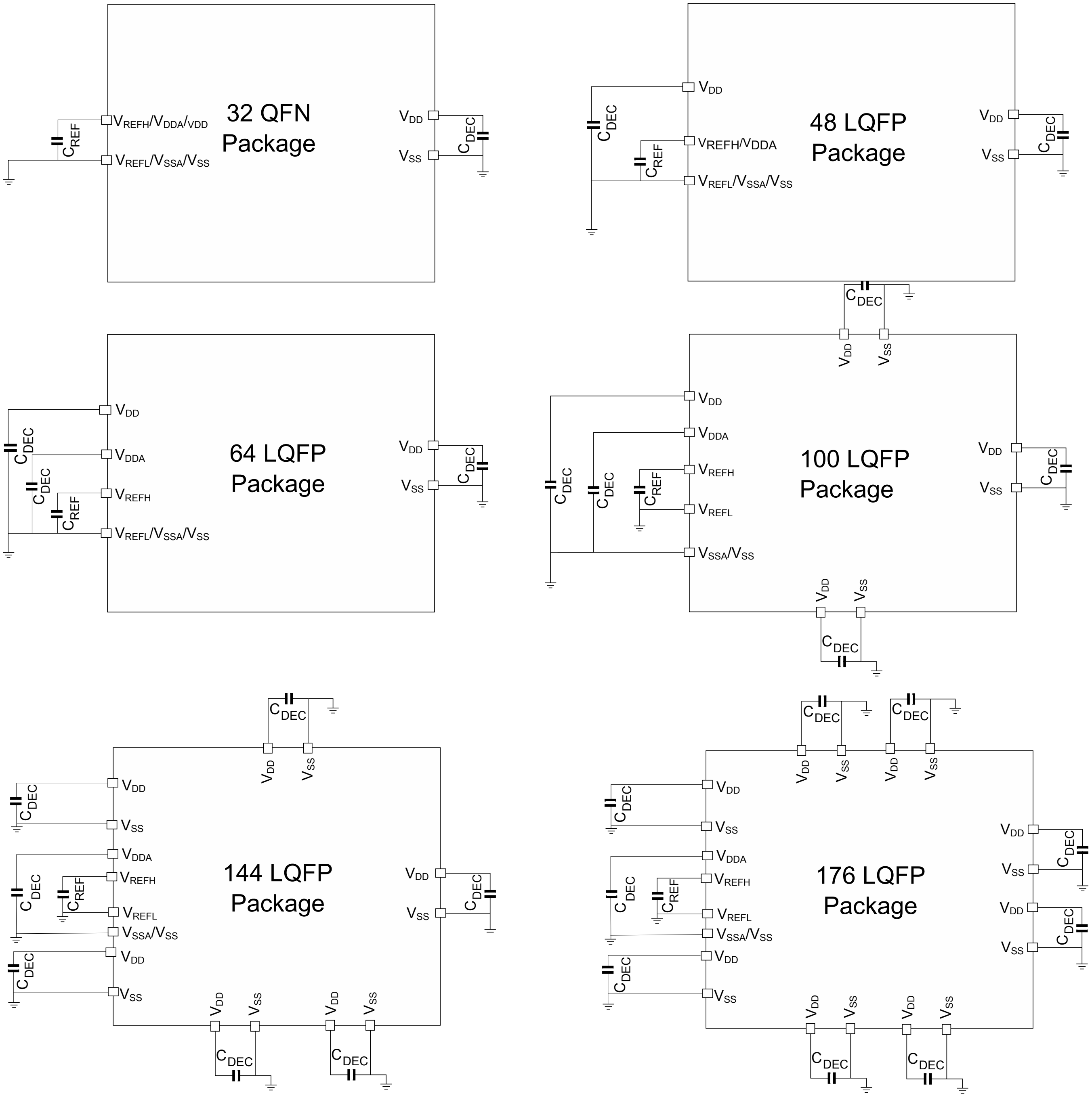
4.3 Thermal operating characteristics

Table 3. Thermal operating characteristics for 64 LQFP, 100 LQFP, and 100 MAP-BGA packages.

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$T_{A\ \text{C-Grade Part}}$	Ambient temperature under bias	–40	—	85[1]	℃
$T_{J\ \text{C-Grade Part}}$	Junction temperature under bias	–40	—	105[1]	℃
$T_{A\ \text{V-Grade Part}}$	Ambient temperature under bias	–40	—	105[1]	℃
$T_{J\ \text{V-Grade Part}}$	Junction temperature under bias	–40	—	125[1]	℃
$T_{A\ \text{M-Grade Part}}$	Ambient temperature under bias	–40	—	125[2]	℃
$T_{J\ \text{M-Grade Part}}$	Junction temperature under bias	–40	—	135[2]	℃

1. Values mentioned are measured at ≤ 112 MHz in HSRUN mode.
2. Values mentioned are measured at ≤ 80 MHz in RUN mode.

4.4 Power and ground pins



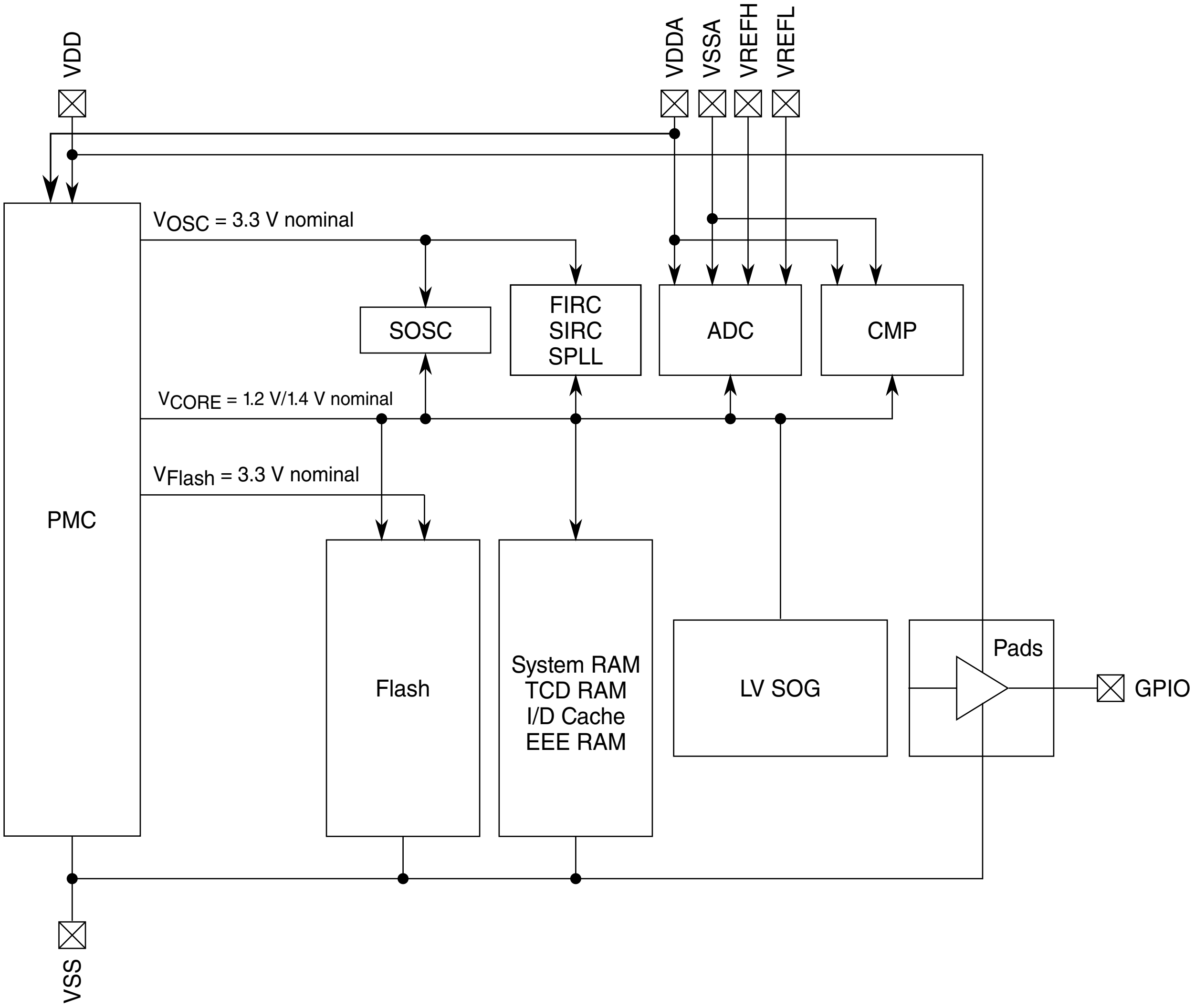
NOTE: V_{DD} and V_{DDA} must be shorted to a common source on PCB

Figure 5. Pinout decoupling

Table 4. Supplies decoupling capacitors [1], [2]

Symbol	Description	Min. [3]	Typ.	Max.	Unit
C_{REF}, [4], [5]	ADC reference high decoupling capacitance	70	100	—	nF
C_{DEC}[5], [6], [7]	Recommended decoupling capacitance	70	100	—	nF

1. V_{DD} and V_{DDA} must be shorted to a common source on PCB. The differential voltage between V_{DD} and V_{DDA} is for RF-AC only. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC. All V_{SS} pins should be connected to common ground at the PCB level.
2. All decoupling capacitors must be low ESR ceramic capacitors (for example X7R type).
3. Minimum recommendation is after considering component aging and tolerance.
4. For improved performance, it is recommended to use 10 µF, 0.1 µF and 1 nF capacitors in parallel.
5. All decoupling capacitors should be placed as close as possible to the corresponding supply and ground pins.
6. Contact your local Field Applications Engineer for details on best analog routing practices.
7. The filtering used for decoupling the device supplies must comply with the following best practices rules:
    - The protection/decoupling capacitors must be on the path of the trace connected to that component.
    - No trace exceeding 1 mm from the protection to the trace or to the ground.
    - The protection/decoupling capacitors must be as close as possible to the input pin of the device (maximum 2 mm).
    - The ground of the protection is connected as short as possible to the ground plane under the integrated circuit.



*Note: VSSA and VSS are shorted at package level

Figure 6. Power diagram

4.5 LVR, LVD and POR operating requirements

Table 5. V_{DD} supply LVR, LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Rising and falling V_{DD} POR detect voltage	1.1	1.6	2.0	V	
V_{LVR}	LVR falling threshold (RUN, HSRUN, and STOP modes)	2.50	2.58	2.7	V	
V_{LVR_HYST}	LVR hysteresis	—	45	—	mV	1
V_{LVR_LP}	LVR falling threshold (VLPS/VLPR modes)	1.97	2.22	2.44	V	
V_{LVD}	Falling low-voltage detect threshold	2.8	2.875	3	V	
V_{LVD_HYST}	LVD hysteresis	—	50	—	mV	1

Table continues on the next page...

Table 5. V_{DD} supply LVR, LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{LVW}	Falling low-voltage warning threshold	4.19	4.305	4.5	V	
V_{LVW_HYST}	LVW hysteresis	—	75	—	mV	1
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	

1. Rising threshold is the sum of falling threshold and hysteresis voltage.

4.6 Power mode transition operating behaviors

All specifications in the following table assume this clock configuration:

- RUN Mode:
  - Clock source: FIRC
  - SYS_CLK/CORE_CLK = 48 MHz
  - BUS_CLK = 48 MHz
  - FLASH_CLK = 24 MHz
- HSRUN Mode:
  - Clock source: SPLL
  - SYS_CLK/CORE_CLK = 112 MHz
  - BUS_CLK = 56 MHz
  - FLASH_CLK = 28 MHz
- VLPR Mode:
  - Clock source: SIRC
  - SYS_CLK/CORE_CLK = 4 MHz
  - BUS_CLK = 4 MHz
  - FLASH_CLK = 1 MHz
- STOP1/STOP2 Mode:
  - Clock source: FIRC
  - SYS_CLK/CORE_CLK = 48 MHz
  - BUS_CLK = 48 MHz
  - FLASH_CLK = 24 MHz
- VLPS Mode: All clock sources disabled [1]

Table 6. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 2.7 V to execution of the first instruction across the operating temperature range of the chip.	—	325	—	μs

Table continues on the next page...

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[1]
- For S32K11x – FIRC/SOSC
- For S32K14x – FIRC/SOSC/SPLL

Table 6. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
	VLPS → RUN	8	—	17	µs
	STOP1 → RUN	0.07	0.075	0.08	µs
	STOP2 → RUN	0.07	0.075	0.08	µs
	VLPR → RUN	19	—	26	µs
	VLPR → VLPS	5.1	5.7	6.5	µs
	VLPS → VLPR	18.8	23	27.75	µs
	RUN → Compute operation	0.72	0.75	0.77	µs
	HSRUN → Compute operation	0.3	0.31	0.35	µs
	RUN → STOP1	0.35	0.38	0.4	µs
	RUN → STOP2	0.2	0.23	0.25	µs
	RUN → VLPS	0.3	0.35	0.4	µs
	RUN → VLPR	3.5	3.8	5	µs
	VLPS → Asynchronous DMA Wakeup	105	110	125	µs
	STOP1 → Asynchronous DMA Wakeup	1	1.1	1.3	µs
	STOP2 → Asynchronous DMA Wakeup	1	1.1	1.3	µs
	Pin reset → Code execution	—	214	—	µs

NOTE

HSRUN should only be used when frequencies in excess of 80 MHz are required. When using 80 MHz and below, RUN mode is the recommended operating mode.

4.7 Power consumption

The following table shows the power consumption targets for the device in various mode of operations. Attached *S32K1xx_Power_Modes _Configuration.xlsx* details the modes used in gathering the power consumption data stated in the following table Table 7. For full functionality refer to table: Module operation in available power modes of the *Reference Manual*.

Table 7. Power consumption (Typicals unless stated otherwise) [1]

Chip/Device	Ambient Temperature (°C)		VLPS (µA) [2]		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) [3]		IDD/MHz (µA/MHz) [4]
			Peripherals disabled [5]	Peripherals enabled	Peripherals disabled [6]	Peripherals enabled use case 1 [6]	Peripherals enabled use case 2 [7]			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
S32K116	25	Typ	26	40	1.05	1.07	TBD	6.3	7.2	11.8	20.3	NA						245
	85	Typ	76	93	1.1	1.11	TBD	6.6	7.5	12	20.6							251
		Max	287	300	1.39	1.4	NA	8	8.9	13.4	22.1							279
	105	Typ	139	164	1.15	1.16	TBD	6.8	7.7	12.3	20.8							255
		Max	590	603	1.68	1.69	NA	9.2	10.1	14.5	23.1							302
	125	Typ	NA	NA	NA	NA	TBD	NA	NA	NA	NA							NA
		Max	891	904	2.02	2.04	NA	10.4	11.3	15.6	24.1							325
S32K118	25	Typ	26	38	1.9	2.5	TBD	7	12	TBD	TBD	NA						TBD
	105	Typ	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD							TBD
		Max	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD							TBD
	125	Max	TBD	TBD	TBD	TBD	TBD	TBD	TBD	TBD	42							TBD
S32K142	25	Typ	29	40	1.17	1.21	2.19	6.4	7.4	17.3	24.6	24.5	31.3	28.8	37.5	40.5	52.2	360
	85	Typ	128	137	1.48	1.51	2.31	7	8	17.6	24.9	25	31.6	29.1	37.7	41.1	52.5	364
		Max	335	360	1.87	1.89	NA	8.6	9.4	22	28.2	26.9	33.5	32	40	44	55.6	400
	105	Typ	240	257	1.58	1.61	2.44	7.6	8.3	18.3	25.7	25.5	31.9	29.8	38	41.5	53.1	373
		Max	740	791	2.32	2.34	NA	9.9	10.9	23.1	30.2	27.8	35.3	33.8	40.7	44.9	57.4	423
	125	Typ	NA	NA	NA	NA	2.84	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA

Table continues on the next page...

Table 7. Power consumption (Typicals unless stated otherwise) [1] (continued)

Chip/Device	Ambient Temperature (°C)		VLPS (µA) [2]		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) [3]		IDD/MHz (µA/MHz) [4]
			Peripherals disabled [5]	Peripherals enabled	Peripherals disabled [6]	Peripherals enabled use case 1 [6]	Peripherals enabled use case 2 [7]			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
		Max	1637	1694	3.1	3.21	NA	12.7	13.7	25	32.9	30.7	38.8	36	43.8	NA		450
S32K144	25	Typ	29.8	42	1.48	1.50	2.91	7	7.7	19.7	26.9	25.1	33.3	30.2	39.6	43.3	55.6	378
	85	Typ	150	159	1.72	1.85	3.08	7.2	8.1	20.4	27.1	26.1	33.5	30.5	40	43.9	56.1	381
		Max	359	384	2.60	2.65	NA	9.2	9.9	23.2	29.6	29.3	36.2	34.8	42.1	46.3	59.7	435
	105	Typ	256	273	1.80	2.10	3.23	7.8	8.5	20.6	27.4	26.6	33.8	31.2	40.5	44.8	57.1	390
		Max	850	900	2.65	2.70	NA	10.3	11.1	23.9	30.6	30.3	37.3	35.6	43.5	47.9	61.3	445
	125	Typ	NA	NA	NA	NA	3.65	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	1960	1998	3.18	3.25	NA	12.9	13.8	26.9	33.6	35	40.3	38.7	46.8	NA		484
S32K146	25	Typ	37	47	1.57	1.61	3.3	8	9.2	23.4	31.4	30.5	40.2	36.2	47.6	52	68.3	452
	85	Typ	207	209	1.79	1.83	3.54	8.9	10.1	24.4	32.4	31.5	41.3	37.2	48.7	53.3	69.8	465
		Max	974	981	3.32	3.38	NA	12.7	13.9	29.3	37.9	36.7	47	42.4	54.4	60.3	78	530
	105	Typ	419	422	1.99	2.04	3.78	9.8	11	25.3	33.4	32.5	42.2	38.1	49.6	54.4	70.8	477
		Max	2004	2017	4.06	4.13	NA	17.1	18.3	34.1	42.6	41.3	51.4	46.9	58.8	65.7	82.8	587
	125	Typ	NA	NA	NA	NA	4.44	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	3358	3380	5.28	5.38	NA	22.6	23.7	40.2	48.8	47.3	57.4	52.8	64.8	NA		660
S32K148[8]	25	Typ	38	54	2.17	2.20	3.45	8.5	9.6	27.6	34.9	35.5	45.3	42.1	57.7	60.3	83.3	526
	85	Typ	336	357	2.30	2.35	3.74	10.1	11.1	29.1	37.0	36.8	46.6	43.4	59.9	62.9	88.7	543

Table continues on the next page...

Table 7. Power consumption (Typicals unless stated otherwise) [1] (continued)

Chip/Device	Ambient Temperature (°C)		VLPS (µA) [2]		VLPR (mA)			STOP1 (mA)	STOP2 (mA)	RUN@48 MHz (mA)		RUN@64 MHz (mA)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA) [3]		IDD/MHz (µA/MHz) [4]
			Peripherals disabled [5]	Peripherals enabled	Peripherals disabled [6]	Peripherals enabled use case 1 [6]	Peripherals enabled use case 2 [7]			Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	Peripherals enabled	
		Max	1660	1736	3.48	3.55	NA	14.5	15.6	34.8	43.6	41.9	53.9	48.7	65.1	70.4	96.1	609
	105	Typ	560	577	2.49	2.54	4.03	10.9	11.9	29.8	37.8	37.6	47.5	45.2	61.5	63.8	89.1	565
		Max	2945	2970	4.40	4.47	NA	18.0	19.0	38.4	46.8	44.9	55.3	51.6	66.8	73.6	97.4	645
	125	Typ	NA	NA	NA	NA	4.85	NA	NA	NA	NA	NA	NA	NA	NA	NA		NA
		Max	3990	4166	6.00	6.08	NA	23.4	24.5	44.3	52.5	50.9	61.3	57.5	71.6	NA		719

1. Typical current numbers are indicative for typical silicon process and may vary based on the silicon distribution and user configuration. Typical conditions assumes $V_{DD} = V_{DDA} = V_{REFH} = 5$ V, temperature = 25 °C and typical silicon process unless otherwise stated. All output pins are floating and On-chip pulldown is enabled for all unused input pins.
2. Current numbers are for reduced configuration and may vary based on user configuration and silicon process variation.
3. HSRUN mode must not be used at 125°C. Max ambient temperature for HSRUN mode is 105°C.
4. Values mentioned for S32K14x devices are measured at RUN@80 MHz with peripherals disabled and values mentioned for S32K11x devices are measured at RUN@48 MHz with peripherals disabled.
5. With PMC_REGSC[CLKBIASDIS] set to 1. See Reference Manual for details.
6. Data collected using RAM
7. Numbers on limited samples size and data collected with Flash
8. The S32K148 data points assume that ENET/QuadSPI/SAI etc. are inactive.

Table 8. VLPS additional use-case power consumption at typical conditions

Use-case	Description	Temp.	Device						Unit
			S32K116	S32K118	S32K142	S32K144	S32K146	S32K148	
VLPS and RTC	• Clock source: LPO or RTC_CLKIN	25	TBD	TBD	30	30	30	40	µA
		85	TBD	TBD	110	170	180	240	µA
		105	TBD	TBD	230	330	350	490	µA
		125	TBD	TBD	570	680	810	1250	µA
VLPS and LPUART TX/RX	• Clock source: SIRC • Transmiting or receiving continuously using DMA • Baudrate: 19.2 kbps	25	TBD	TBD	230	230	250	250	µA
		85	TBD	TBD	320	400	410	490	µA
		105	TBD	TBD	490	550	600	850	µA
		125	TBD	TBD	890	1070	1250	1960	µA
VLPS and LPUART wake-up	• Clock source: SIRC • Wake-up address feature enabled • Baudrate: 19.2 kbps	25	TBD	TBD	100	100	110	110	µA
		85	TBD	TBD	170	240	280	350	µA
		105	TBD	TBD	260	400	480	600	µA
		125	TBD	TBD	530	580	1000	1280	µA
VLPS and LPI2C master	• Clock Source: SIRC • Transmit/receive using DMA • Baudrate: 100 kHz	25	TBD	TBD	670	690	820	900	µA
		85	TBD	TBD	880	960	1220	1370	µA
		105	TBD	TBD	1080	1250	1660	2060	µA
		125	TBD	TBD	1970	1980	2860	3690	µA
VLPS and LPI2C slave wake-up	• Clock source: SIRC • Wake-up address feature enabled • Baudrate: 100 kHz	25	TBD	TBD	250	250	270	280	µA
		85	TBD	TBD	340	340	410	510	µA
		105	TBD	TBD	430	430	610	810	µA
		125	TBD	TBD	740	760	1170	1540	µA
VLPS and LPSPI master	• Clock source: SIRC • Transmit/receive using DMA • Baudrate: 500 kHz	25	TBD	TBD	2.99	3.19	3.75	4.11	mA
		85	TBD	TBD	3.26	3.7	4.35	4.93	mA
		105	TBD	TBD	3.5	4.2	4.93	5.74	mA
		125	TBD	TBD	3.93	4.63	5.97	7.38	mA
VLPS and LPIT	• Clock source: SIRC • 1 channel enable • Mode: 32-bit periodic counter	25	TBD	TBD	100	100	120	130	µA
		85	TBD	TBD	190	250	260	320	µA
		105	TBD	TBD	310	410	440	570	µA
		125	TBD	TBD	640	750	910	1280	µA

The following table shows the power consumption targets for S32K148 in various mode of operations measure at 3.3 V.

Table 9. Power consumption at 3.3 V

Chip/Device	Ambient Temperature (°C)		RUN@80 MHz (mA)		HSRUN@112 MHz (mA)[1]	
			Peripherals enabled + QSPI	Peripherals enabled + ENET + SAI	Peripherals enabled + QSPI	Peripherals enabled + ENET + SAI
S32K148	25	Typ	67.3	79.1	89.8	105.5
	85	Typ	67.4	79.2	95.6	105.9
		Max	82.5	88.2	109.7	117.4
	105	Typ	68.0	79.8	96.6	106.7
		Max	80.3	89.1	109.0	119.0
	125	Max	83.5	94.7	NA	

1. HSRUN mode must not be used at 125°C. Max ambient temperature for HSRUN mode is 105°C.

4.8 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	– 4000	4000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model				2
	All pins except the corner pins	– 500	500	V	
	Corner pins only	– 750	750	V	
I_{LAT}	Latch-up current at ambient temperature of 125 °C	– 100	100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

4.9 EMC radiated emissions operating behaviors

EMC measurements to IC-level IEC standards are available from NXP on request.

5 I/O parameters

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

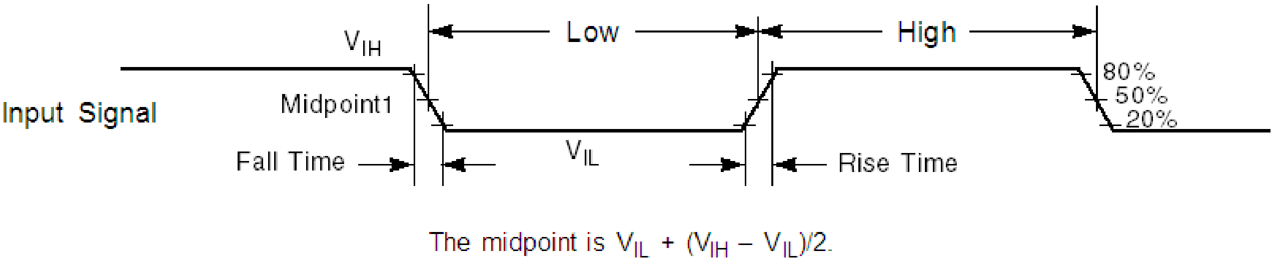

Figure 7. Input signal measurement reference

5.2 General AC specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and timers.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, passive filter disabled) — Asynchronous path	50	—	ns	3
WFRST	$\overline{\text{RESET}}$ input filtered pulse	—	10	ns	4
WNFRST	$\overline{\text{RESET}}$ input not filtered pulse	Maximum of (100 ns, bus clock period)	—	ns	5

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop and VLPS modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater of synchronous and asynchronous timing must be met.
3. These pins do not have a passive filter on the inputs. This is the shortest pulse width that is guaranteed to be recognized.
4. Maximum length of $\overline{\text{RESET}}$ pulse which will be filtered by internal filter.
5. Minimum length of $\overline{\text{RESET}}$ pulse, guaranteed not to be filtered by the internal filter. This number depends on bus clock period also. For example, in VLPR mode bus clock is 4 MHz, which make clock period of 250 ns. In this case, minimum pulse width which will cause reset is 250 ns. For faster bus clock frequencies which have clock period less than 100 ns, the minimum pulse width not filtered will be 100 ns.

5.3 DC electrical specifications at 3.3 V Range

NOTE

For details on the pad types defined in Table 11 and Table 12, see Reference Manual section *IO Signal Table* and IO Signal Description Input Multiplexing sheet(s) attached with Reference Manual.

Table 11. DC electrical specifications at 3.3 V Range

Symbol	Parameter	Value			Unit	Notes
		Min.	Typ.	Max.		
V_{DD}	I/O Supply Voltage	2.7	3.3	4	V	1
V_{ih}	Input Buffer High Voltage	0.7 × V_{DD}	—	V_{DD} + 0.3	V	2
V_{il}	Input Buffer Low Voltage	V_{SS} – 0.3	—	0.3 × V_{DD}	V	3
V_{hys}	Input Buffer Hysteresis	0.06 × V_{DD}	—	—	V	
Ioh_{GPIO} $Ioh_{GPIO\text{-}HD\_DSE\_0}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	3.5	—	—	mA	
Iol_{GPIO} $Iol_{GPIO\text{-}HD\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	3	—	—	mA	
$Ioh_{GPIO\text{-}HD\_DSE\_1}$	I/O current source capability measured when pad V_{oh} = (V_{DD} – 0.8 V)	14	—	—	mA	4
$Iol_{GPIO\text{-}HD\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	12	—	—	mA	4
$Ioh_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	9.5	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	10	—	—	mA	5
$Ioh_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{oh}=V_{DD}-0.8 V	16	—	—	mA	5
$Iol_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	15.5	—	—	mA	5
IOHT	Output high current total for all ports	—	—	100	mA	
IIN	Input leakage current (per pin) for full temperature range at V_{DD} = 3.3 V					6
	All pins other than high drive port pins		0.005	0.5	µA	
	High drive port pins [7]		0.010	0.5	µA	
R_{PU}	Internal pullup resistors	20		60	kΩ	8
R_{PD}	Internal pulldown resistors	20		60	kΩ	9

1. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
2. For reset pads, same V_{ih} levels are applicable
3. For reset pads, same V_{il} levels are applicable
4. The value given is measured at high drive strength mode. For value at low drive strength mode see the Ioh_Standard value given above.
5. For refernce only. Run simulations with the IBIS model and custom board for accurate results.

6. Several I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only. For details see IO Signal Description Input Multiplexing sheet(s) attached with the *Reference Manual*.
7. When using ENET and SAI on S32K148, the overall device limits associated with high drive pin configurations must be respected i.e. On 144-pin LQFP the general purpose pins: PTA10, PTD0, and PTE4 must be set to low drive.
8. Measured at input V = V_{SS}
9. Measured at input V = V_{DD}

5.4 DC electrical specifications at 5.0 V Range

Table 12. DC electrical specifications at 5.0 V Range

Symbol	Parameter	Value			Unit	Notes
		Min.	Typ.	Max.		
V_{DD}	I/O Supply Voltage	4	—	5.5	V	
V_{ih}	Input Buffer High Voltage	0.65 x V_{DD}	—	V_{DD} + 0.3	V	1
V_{il}	Input Buffer Low Voltage	V_{SS} – 0.3	—	0.35 x V_{DD}	V	2
V_{hys}	Input Buffer Hysteresis	0.06 x V_{DD}	—	—	V	
Ioh_{GPIO} $Ioh_{GPIO\text{-}HD\_DSE\_0}$	I/O current source capability measured when pad V_{oh}= (V_{DD} - 0.8 V)	5	—	—	mA	
Iol_{GPIO} $Iol_{GPIO\text{-}HD\_DSE\_0}$	I/O current sink capability measured when pad V_{ol}= 0.8 V	5	—	—	mA	
$Ioh_{GPIO\text{-}HD\_DSE\_1}$	I/O current source capability measured when pad V_{oh} = V_{DD} - 0.8 V	20	—	—	mA	3
$Iol_{GPIO\text{-}HD\_DSE\_1}$	I/O current sink capability measured when pad V_{ol} = 0.8 V	20	—	—	mA	3
$Ioh_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{oh} = V_{DD} - 0.8 V	14.0	—	—	mA	4
$Iol_{GPIO\text{-}FAST\_DSE\_0}$	I/O current sink capability measured when pad V_{ol}= 0.8 V	14.5	—	—	mA	4
$Ioh_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{oh} = V_{DD} - 0.8 V	21	—	—	mA	4
$Iol_{GPIO\text{-}FAST\_DSE\_1}$	I/O current sink capability measured when pad V_{ol}= 0.8 V	20.5	—	—	mA	4
IOHT	Output high current total for all ports	—	—	100	mA	
IIN	Input leakage current (per pin) for full temperature range at V_{DD} = 5.5 V					5
	All pins other than high drive port pins		0.005	0.5	μA	
	High drive port pins		0.010	0.5	μA	
R_{PU}	Internal pullup resistors	20		50	kΩ	6
R_{PD}	Internal pulldown resistors	20		50	kΩ	7

1. For reset pads, same V_{ih} levels are applicable
2. For reset pads, same V_{il} levels are applicable
3. The strong pad I/O pin is capable of switching a 50 pF load up to 40 MHz.
4. For refernce only. Run simulations with the IBIS model and custom board for accurate results.

5. Several I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only. For details refer to *SK3K144_IO_Signal_Description_Input_Multiplexing.xlsx* attached with the *Reference Manual*.
6. Measured at input V = V_{SS}
7. Measured at input V = V_{DD}

5.5 AC electrical specifications at 3.3 V range

Table 13. AC electrical specifications at 3.3 V Range

Symbol	DSE	Rise time (nS) [1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max.	Min.	Max.	
tRF_{GPIO}	NA	3.2	14.5	3.4	15.7	25
		5.7	23.7	6.0	26.2	50
		20.0	80.0	20.8	88.4	200
$tRF_{GPIO-HD}$	0	3.2	14.5	3.4	15.7	25
		5.7	23.7	6.0	26.2	50
		20.0	80.0	20.8	88.4	200
	1	1.5	5.8	1.7	6.1	25
		2.4	8.0	2.6	8.3	50
		6.3	22.0	6.0	23.8	200
$tRF_{GPIO-FAST}$	0	0.6	2.8	0.5	2.8	25
		3.0	7.1	2.6	7.5	50
		12.0	27.0	10.3	26.8	200
	1	0.4	1.3	0.38	1.3	25
		1.5	3.8	1.4	3.9	50
		7.4	14.9	7.0	15.3	200

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.
2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.6 AC electrical specifications at 5 V range

Table 14. AC electrical specifications at 5 V Range

Symbol	DSE	Rise time (nS)[1]		Fall time (nS) [1]		Capacitance (pF) [2]
		Min.	Max .	Min.	Max.	
tRF_{GPIO}	NA	2.8	9.4	2.9	10.7	25
		5.0	15.7	5.1	17.4	50
		17.3	54.8	17.6	59.7	200
$tRF_{GPIO-HD}$	0	2.8	9.4	2.9	10.7	25
		5.0	15.7	5.1	17.4	50

Table continues on the next page...